

150U/150UR

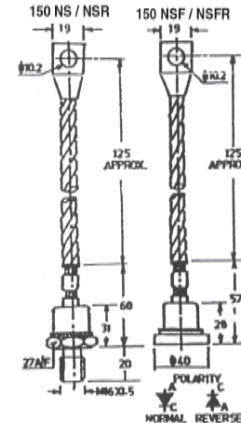
SILICON POWER DIODE

**NAINA****DO - 8****FEATURES**

- Diffused Series
- Available in Normal & Reverse Polarity
- Industrial Grade
- Available In Avalanche Characteristic

ELECTRICAL SPECIFICATIONS

I_F	Maximum Average Forward Current $T_c=125^\circ\text{C}$	150A
V_{FM}	Maximum peak forward voltage drop @ Rated $I_F(AV)$	1.4V
I_{FSM}	Maximum peak one cycle (non-rep) surge current 10 m sec	3000A
I_{FRM}	Maximum peak repetitive surge current	750A
I^2t	Maximum I^2t rating (non-rep.) for 5 to 10 msec.	45,000 A ² Sec

**THERMAL MECHANICAL SPECIFICATIONS**

θ_{JC}	Maximum thermal resistance Junction to case	0.25°C/W
T_j	Operating Junction Temp.	-65°C to 150°C
T_{stg}	Storage temperature	-65°C to 200°C
	Mounting torque (Non-lubricated threads)	2.0 M-kg min, 3.0 M-kg max
W	Approx, weight	150 gms.

ELECTRICAL RATINGS

TYPE	150U/150UR	10	20	40	60	80	100	120	140	160
V_{RRM}	Max. repetitive peak reverse voltage (v)	100	200	400	600	800	1000	1200	1400	1600
$V_R(RMS)$	Max. R.M.S. reverse voltage (V)	70	140	280	420	560	700	840	980	1120
V_R	Max. D.C. Blocking Voltage (V)	100	200	400	600	800	1000	1200	1400	1600
	Recommended R.M.S. working Voltage(v)	40	80	160	240	320	400	480	560	640
$I_R(AV)$	Max. Average reverse leakage current @ V_{RRM} T_c 25°C (uA)	200	200	200	200	200	200	200	200	200

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